

HAT2119H

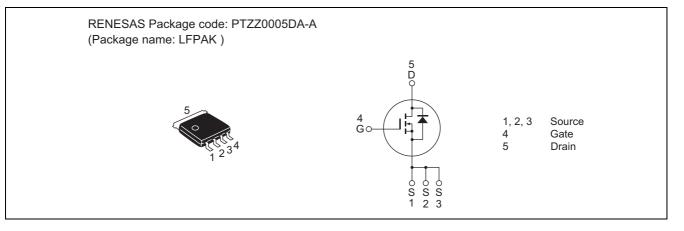
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G0176-0300 Rev.3.00 Dec 19, 2006

Features

- Low drive current.
- Low on-resistance
- www.DataSheet4U.Low profile

Outline



Absolute Maximum Ratings

| | | | $(Ta = 25^{\circ}C)$ |
|---|----------------------------------|-------------|----------------------|
| Item | Symbol | Ratings | Unit |
| Drain to source voltage | V _{DSS} | 250 | V |
| Gate to source voltage | V _{GSS} | ±30 | V |
| Drain current | I _D | 5 | А |
| Drain peak current | I _{D(pulse)} Note1 | 20 | А |
| Body-drain diode reverse drain current | I _{DR} | 5 | А |
| Body-drain diode reverse drain peak current | I _{DR(pulse)} Note1 | 20 | А |
| Avalanche current | I _{AP} ^{Note3} | 5 | А |
| Avalanche energy | E _{AR} ^{Note3} | 1.5 | mJ |
| Channel dissipation | Pch Note2 | 20 | W |
| Channel to case thermal impedance | θch-c | 6.25 | °C/W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = $25^{\circ}C$

3. STch = 25° C, Tch $\leq 150^{\circ}$ C



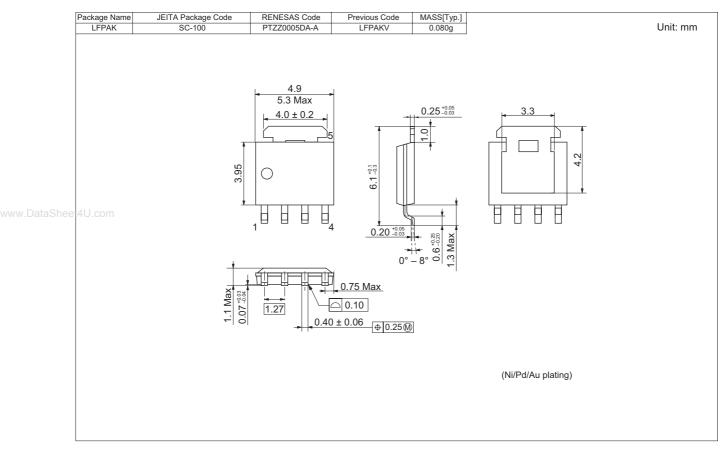
Electrical Characteristics

| | | | | | | $(Ta = 25^{\circ}C)$ |
|--|----------------------|-----|------|------|------|--|
| Item | Symbol | Min | Тур | Max | Unit | Test conditions |
| Drain to source breakdown voltage | V _{(BR)DSS} | 250 | — | _ | V | $I_D = 10 \text{ mA}, V_{GS} = 0$ |
| Zero gate voltage drain current | I _{DSS} | — | — | 1 | μA | $V_{DS} = 250 \text{ V}, V_{GS} = 0$ |
| Gate to source leak current | I _{GSS} | — | — | ±0.1 | μΑ | V_{GS} = ±30 V, V_{DS} = 0 |
| Gate to source cutoff voltage | V _{GS(off)} | 3.0 | — | 4.0 | V | $V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$ |
| Forward transfer admittance | y _{fs} | 2.0 | 4.0 | | S | $I_D = 2.5 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$ |
| Static drain to source on state resistance | R _{DS(on)} | — | 0.48 | 0.63 | Ω | $I_D = 2.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$ |
| Input capacitance | Ciss | — | 450 | | pF | V _{DS} = 25 V |
| Output capacitance | Coss | — | 60 | | pF | V _{GS} = 0 f = 1 MHz |
| Reverse transfer capacitance | Crss | — | 12 | | pF | |
| Turn-on delay time | t _{d(on)} | — | 19 | | ns | I _D = 2.5 A |
| Rise time | tr | — | 10 | _ | ns | $V_{GS} = 10 V$ $R_L = 50 \Omega$ $Rg = 10 \Omega$ |
| Turn-off delay time | t _{d(off)} | — | 48 | _ | ns | |
| Fall time | t _f | — | 10 | _ | ns | |
| Total gate charge | Qg | — | 14 | | nC | V _{DD} = 200 V |
| Gate to source charge | Qgs | — | 2.5 | _ | nC | V _{GS} = 10 V I _D = 5 A |
| Gate to drain charge | Qgd | — | 7 | _ | nC | |
| Body-drain diode forward voltage | V _{DF} | _ | 0.85 | 1.30 | V | $I_F = 5 \text{ A}, V_{GS} = 0^{Note4}$ |
| Body-drain diode reverse recovery time | t _{rr} | _ | 95 | _ | ns | $I_F = 5 \text{ A}, V_{GS} = 0$ |
| | | | | | | di⊧/dt = 100 A/µs |

Notes: 4. Pulse test



Package Dimensions



Ordering Information

| Part No. | Quantity | Shipping Container |
|---------------|----------|--------------------|
| HAT2119H-EL-E | 2500 pcs | Taping |

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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